Unit: mm

TOSHIBA Field Effect Transistor Silicon N Channel Junction Type

2SK246

For Constant Current, Impedance Converter and DC-AC High Input Impedance Amplifier Circuit Applications

- High breakdown voltage: $V_{\rm GDS} = -50 \text{ V}$
- High input impedance: $I_{GSS} = -1$ nA (max) ($V_{GS} = -30$ V)

Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Gate-drain voltage	V_{GDS}	-50	V
Gate current	IG	10	mA
Drain power dissipation	P_{D}	300	mW
Junction temperature	Tj	125	°C
Storage temperature range	T _{stg}	-55~125	°C

1. SOURCE 2. GATE 3. DRAIN JEDEC TO-92 JEITA 5.1 MAX. 0.45 1.27 1.27 XVW L' 7 VAN L' 7

2-5F1C

Weight: 0.21 g (typ.)

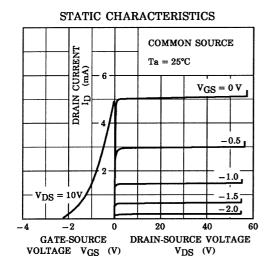
TOSHIBA

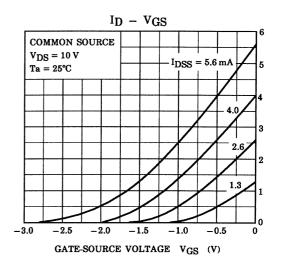
Electrical Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate cut-off current	I _{GSS}	$V_{GS} = -30 \text{ V}, V_{DS} = 0$	_	_	-1.0	nA
Gate-drain breakdown voltage	V (BR) GDS	$V_{DS} = 0$, $I_G = -100 \mu A$	-50	_	_	V
Drain current	I _{DSS} (Note)	V _{DS} = 10 V, V _{GS} = 0	1.2	_	14	mA
Gate-source cut-off voltage	V _{GS} (OFF)	$V_{DS} = 10 \text{ V}, I_D = 0.1 \mu\text{A}$	-0.7	_	-6.0	V
Forward transfer admittance	Yfs	$V_{DS} = 10 \text{ V}, V_{GS} = 0, f = 1 \text{ kHz}$	1.5	_	_	mS
Input capacitance	C _{iss}	V _{DS} = 10 V, V _{GS} = 0, f = 1 MHz	_	9.0	_	pF
Reverse transfer capacitance	C _{rss}	V _{DG} = 10 V, I _D = 0, f = 1 MHz	_	2.5	_	pF

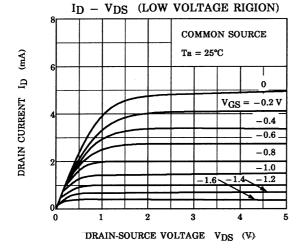
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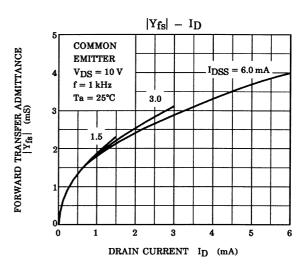
Note: I_{DSS} classification Y: 1.2~3.0 mA, GR: 2.6~6.5 mA, BL: 6~14 mA

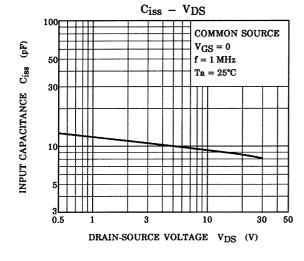


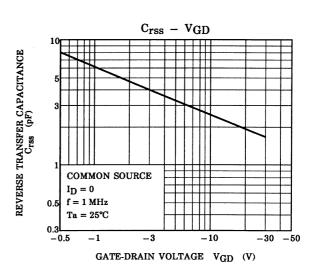


DRAIN CURRENT ID (mA)

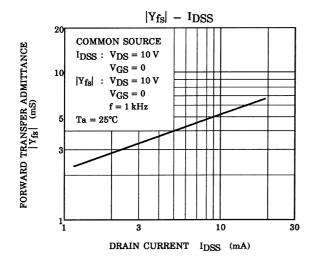


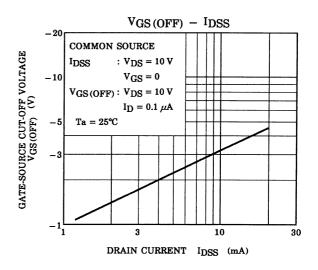


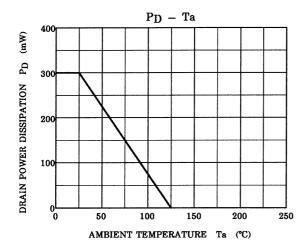




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